

SLA4313

NPN
PNP Silicon Epitaxial Planar

Absolute maximum ratings

($T_a = 25$)

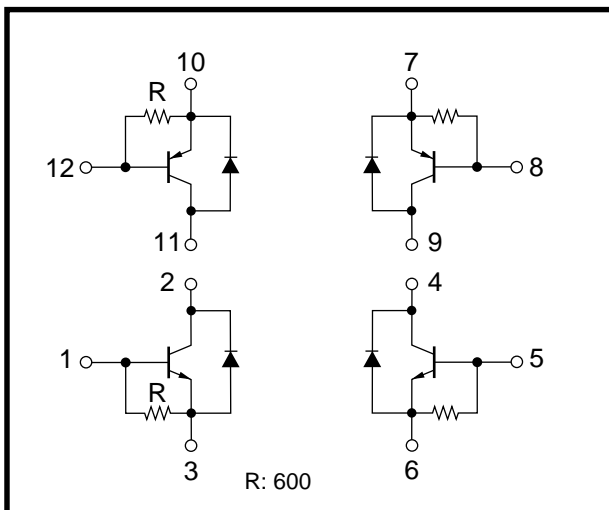
Parameter	Symbol	NPN	PNP	Unit
Collector-Base Voltage	V_{CB0}	35	- 35	V
Collector-Emitter Voltage	V_{CE0}	35	- 35	V
Emitter-Base Voltage	V_{EB0}	6	- 6	V
Collector Current	I_C	5	- 5	A
Collector Current	I_{CP}	8 (P_w 1ms, D_u 50%)		A
Base Current	I_B	1	- 1	A
Total Power Dissipation	P_T	5 ($T_a = 25$)		W
		25 ($T_c = 25$)		
Isolation Voltage	V_{ISO}	1000 (Between fin and lead pin, AC)		Vrms
Storage Temperature	T_{stg}	- 40 to + 150		

Electrical characteristics

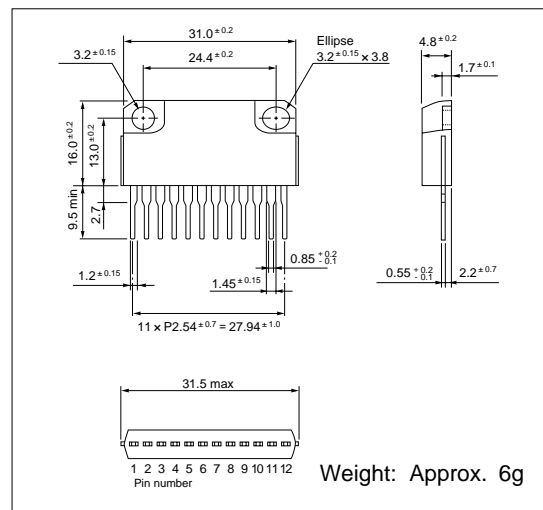
($T_a = 25$)

Parameter	Symbol	NPN	PNP
Collector Cut-off Current	I_{CBO}	10 μ A max ($V_{CB} = 35V$)	- 10 μ A max ($V_{CB} = - 35V$)
Emitter Cut-off Current	I_{EBO}	20mA max ($V_{EB} = 6V$)	- 20mA max ($V_{EB} = - 6V$)
Collector-Emitter Voltage	V_{CE0}	35V min ($I_C = 25mA$)	- 35V min ($I_C = - 25mA$)
DC Current Gain	h_{FE}	50min ($V_{CE} = 4V, I_C = 3A$)	50min ($V_{CE} = - 4V, I_C = - 3A$)
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	0.5V max ($I_C = 3A, I_B = 100mA$)	- 0.5V max ($I_C = - 3A, I_B = - 100mA$)
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	1.3V max ($I_C = 3A, I_B = 100mA$)	- 1.3V max ($I_C = - 3A, I_B = - 100mA$)
Diode Forward Voltage	V_F	1.8V max ($I_F = 2A$)	1.8V max ($I_F = 2A$)

Equivalent circuit diagram



External dimensions (Unit: mm)



Characteristic Curves

